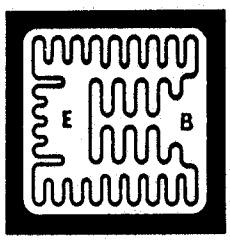
CHIP NUMBER

204



.116" (2.95mm)

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Base: .012" x .044" (0.31mm x 1.12mm)
Emitter: .012" x .058" (0.31mm x 1.47mm)

PNP EPITAXIAL PLANAR POWER TRANSISTOR**

CONTACT METALLIZATION

Base and emitter: > 30,000 Å Aluminum

Collector: Gold
(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL
Size: .220 Diameter (5.59mm)
Thickness: .010" (0.25mm)

BeO PEDESTAL
Size: .142" x .178" (3.61mm x 4.52mm)
Thickness: .028" (0.71mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:
a) the chip be eutectically mounted with gold silicon preform 98/2%.
b) 8 mil (0.203mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 204 in a TO-66 or equivalent case:

V_{CEO}	$V_{CE(s)}$ @	I_C	I_B	h_{FE} @	I_C	V_{CE}
>30V	<1V	8A	0.8A	>10	10A	5V
>45V	<1V	8A	0.8A	>10	10A	5V
>60V	<1V	8A	0.8A	>10	10A	5V
>80V	<1V	8A	0.8A	>10	10A	5V

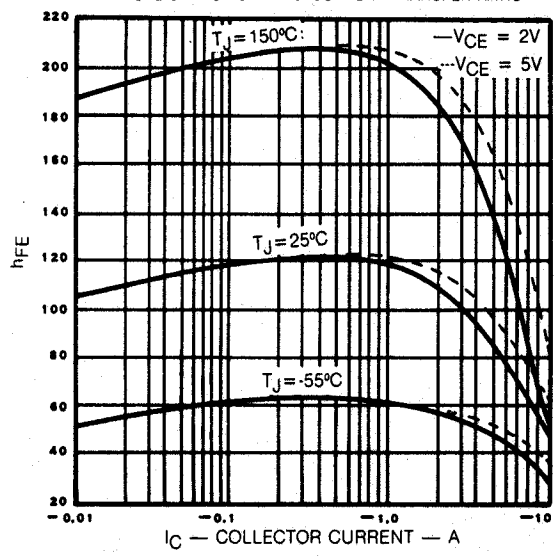
V_{CEO}	V_{CEX}	V_{EBO}	f_T	C_{OBO}	θ_{JC}
>30V	35V	>5V	45MHz	<250pF	<2.5°C/W
>45V	50V	>5V	45MHz	<250pF	<2.5°C/W
>60V	65V	>5V	45MHz	<250pF	<2.5°C/W
>80V	85V	>5V	45MHz	<250pF	<2.5°C/W

TYPICAL DEVICE TYPES: SDT04573, SDT04673

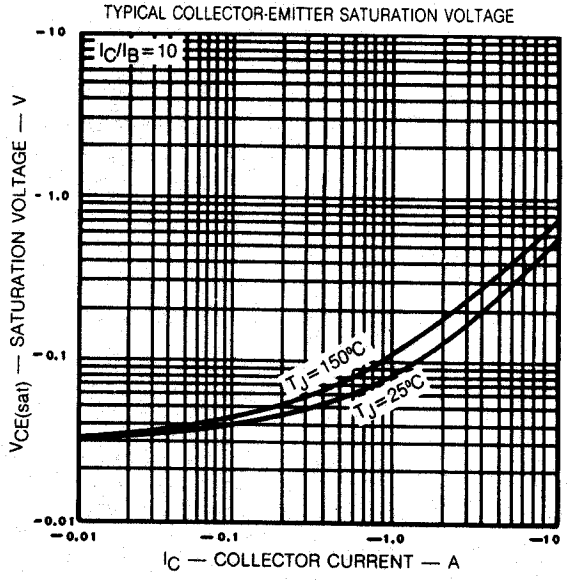
h_{FE} ranges available at I_C = 4A, V_{CE} = 2V, >20 or >40.

**The respective NPN complement is chip number 106.

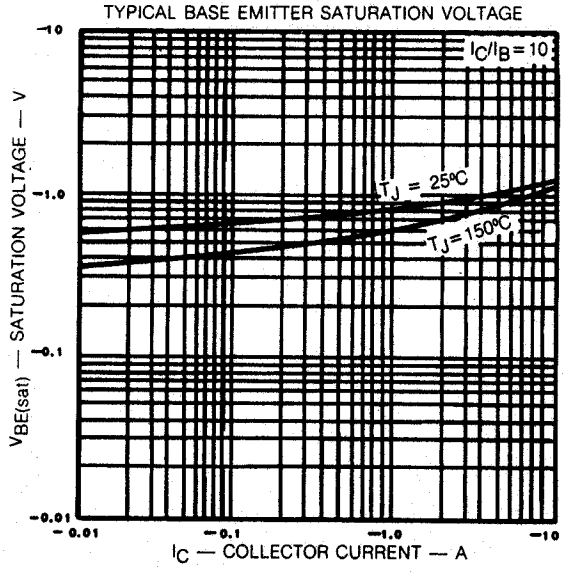
TYPICAL STATIC FORWARD CURRENT TRANSFER RATIO



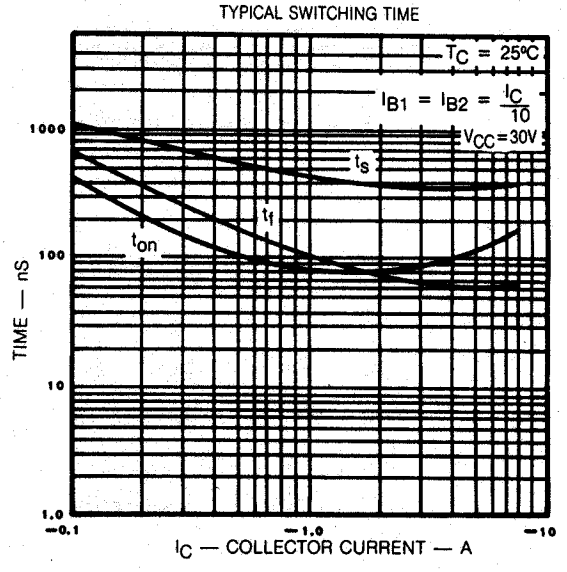
TYPICAL COLLECTOR-EMITTER SATURATION VOLTAGE



TYPICAL BASE EMITTER SATURATION VOLTAGE



TYPICAL SWITCHING TIME



MAXIMUM OPERATING CONDITIONS